

Tuesday, September 5

10:00-12:00 Tutorial (Room D + E (222+223, Bldg.2))
 13:00-17:45 Short CourseA (RoomF (224, Bldg. 2))
 13:00-17:00 Short CourseB (RoomK (234, Bldg. 2))
 17:30-19:30 Welcome Reception (Shirotori Hall, Bldg. 4)

Wednesday, September 6

9:00-12:40 Opening, Award Ceremony and Plenary Sessions (Shirotori Hall, Bldg. 4)

Lunch											
Room A (131 & 132, Bldg. 1)	Room B (133 & 134, Bldg. 1)	Room C (221, Bldg. 2)	Room D (222, Bldg. 2)	Room E (223, Bldg. 2)	Room F (224, Bldg. 2)	Room G (231, Bldg. 2)	Room H (232, Bldg. 2)	Room J (233, Bldg. 2)	Room K (234, Bldg. 2)	Room M (431, Bldg. 4)	Room N (432, Bldg. 4)
14:00-15:15 [A-1] Characterization I: Low Dimensional Devices and Materials	14:00-15:45 Area 1&2&9 Focus Session 4 [B-1] Quantum and cold computing 1		14:00-15:30 Area 6&7 Joint Session [D-1] Perovskite solar cells		14:00-15:45 [F-1] Modeling, Simulation and Characterization	14:00-15:30 [G-1] Advanced Metallization I	14:00-14:45 [H-1] Advanced Materials for Photonics		14:00-15:30 [K-1] Ferroelectric Devices	14:00-15:30 [M-1] Wide Bandgap Materials	14:00-15:30 [N-1] GaN-based Power Devices
Coffee Break											
16:00-17:30 [A-2] Device Application I: Low Dimensional Devices and Materials	16:00-17:30 Area 1&2&9 Focus Session 4 [B-2] Quantum and cold computing 2	16:00-17:00 [C-2] Perovskite solar cells	16:00-17:45 [D-2] Advanced organic and hybrid film devices			16:00-17:30 [G-2] MEMS and Advanced Metallization	16:00-17:00 [H-2] Photonics for AI		16:00-17:30 [K-2] Emerging Memory Devices	16:00-17:30 [M-2] Advanced Materials, Nanofabrication, and Thin Films I	16:00-17:30 [N-2] SiC Processes and Characterizations

18:40-20:40 Banquet (Nagoya Castle, Honmaru Area)

Thursday, September 7

Room A (131 & 132, Bldg. 1)	Room B (133 & 134, Bldg. 1)	Room C (221, Bldg. 2)	Room D (222, Bldg. 2)	Room E (223, Bldg. 2)	Room F (224, Bldg. 2)	Room G (231, Bldg. 2)	Room H (232, Bldg. 2)	Room J (233, Bldg. 2)	Room K (234, Bldg. 2)	Room M (431, Bldg. 4)	Room N (432, Bldg. 4)
9:00-10:00 [A-3] Growth and Synthesis: Low Dimensional Devices and Materials	9:00-10:00 [B-3] Spintronic technologies 1	9:00-10:15 [C-3] Advanced process of oxide semiconductors	9:00-10:15 [D-3] Advanced Lab-on-chip devices	9:00-10:00 [E-3] DRAM	9:00-10:00 [F-3] Ferroelectric Devices		9:00-10:15 [H-3] New/next generation optical sources on silicon	9:00-10:15 [J-3] Advanced Circuits and Systems	9:00-10:15 Area 1&2&8 Focus Session 1 [K-3] CMOS and Memory Applications of Low Dimensional Materials	9:00-10:30 [M-3] Group IV Materials I	9:00-10:15 [N-3] High-speed and Advanced Technologies
Coffee Break											
10:45-11:45 [A-4] Characterization II: Low Dimensional Devices and Materials	10:45-11:45 [B-4] Spintronic technologies 2	10:45-12:00 [C-4] Photovoltaics	10:45-12:00 [D-4] High-sensitive devices for chem/bio detection 1	10:45-12:00 [E-4] 3D NAND	10:45-11:45 [F-4] Innovative Devices and Sensing Technology	10:45-12:00 [G-4] Advanced Metallization II		10:45-12:00 [J-4] Circuit Reliability and Image Sensors	10:45-12:15 Area 1&2&10 Focus Session 2 [K-4] Oxide Semiconductors for Logic and Memory	10:45-12:00 [M-4] Group IV Materials II	10:45-12:00 [N-4] Si-based Power Devices
Lunch											
13:30-14:30 Short Oral Presentation	13:30-14:30 Short Oral Presentation	13:30-14:30 Short Oral Presentation	13:30-14:30 Short Oral Presentation	13:30-14:30 Short Oral Presentation	13:30-14:30 Short Oral Presentation	13:30-14:30 Short Oral Presentation	13:30-14:30 Short Oral Presentation	13:30-14:30 Short Oral Presentation	13:30-14:30 Short Oral Presentation	13:30-14:30 Short Oral Presentation	13:30-14:30 Short Oral Presentation

15:00-17:00 Poster Session (Shirotori Hall, Bldg. 4)

Friday, September 8

17:30-19:30 Rump Sessions (Room F (224, Bldg. 2))

Room A (131 & 132, Bldg. 1)	Room B (133 & 134, Bldg. 1)	Room C (221, Bldg. 2)	Room D (222, Bldg. 2)	Room E (223, Bldg. 2)	Room F (224, Bldg. 2)	Room G (231, Bldg. 2)	Room H (232, Bldg. 2)	Room J (233, Bldg. 2)	Room K (234, Bldg. 2)	Room M (431, Bldg. 4)	Room N (432, Bldg. 4)
			9:00-10:00 [D-5] High-sensitive devices for chem/bio detection 2	9:00-10:15 [E-5] Oxide semiconductor TFTs and technology	9:00-10:15 [F-5] Advanced CMOS: Process Technology	9:00-10:15 Area 1&3 Focus Session 5 [G-5] Heterogenous Integration for High Performance Computing: System, Material, Process and Chiplet I	9:00-10:15 [H-5] Ferroelectric Memory Materials	9:00-10:15 [J-5] AI and Neural Applications	9:00-10:30 Area 2&8&9 Focus Session 3 [K-5] Advanced devices, circuits, and system architectures for future computing systems		9:00-10:15 [N-5] SiC MOS interfaces
Coffee Break											
10:45-12:15 [A-6] Device Application II: Low Dimensional Devices and Materials	10:45-12:15 [B-6] Neuromorphic devices and materials	10:45-12:00 [C-6] Battery&Energy harvesting	10:45-12:15 [D-6] Advanced organic devices	10:45-12:00 [E-6] Thin films for sensors and gate insulators		10:45-12:00 Area 1&3 Focus Session 5 [G-6] Heterogenous Integration for High Performance Computing: System, Material, Process and Chiplet II	10:45-12:00 [H-6] Advanced light sources		10:45-12:00 [K-6] In-Memory and Unconventional Computing 1	10:45-12:00 [M-6] Advanced Materials, Nanofabrication, and Thin Films II	10:45-11:45 [N-6] Diamond-based Devices
Lunch											
13:30-14:45 [A-7] Device Application III: Low Dimensional Devices and Materials		13:30-15:00 [C-7] Thermoelectric devices		13:45-15:00 [E-7] Advanced LTPS TFTs and related technologies	13:30-15:15 [F-7] Advanced CMOS: Device Technology 1		13:30-15:00 [H-7] Si Photonics		13:30-15:00 [K-7] MRAM, FeRAM, and ReRAM	13:30-15:15 [M-7] Advanced Materials, Nanofabrication, and Thin Films III	13:30-15:00 [N-7] Ga2O3-based Devices
Coffee Break											
15:30-16:15 [A-8] Characterization III: Low Dimensional Devices and Materials				15:30-16:15 [E-8] Group IV crystal growth and applications	15:30-16:30 [F-8] Advanced CMOS: Device Technology 2				15:30-16:30 [K-8] In-Memory and Unconventional Computing 2		

- Area Scope
- Area 1: Advanced CMOS: Material Science / Process Engineering / Device Technology
 - Area 2: Advanced and Emerging Memories / New Applications
 - Area 3: Interconnect / 3D Integrations / MEMS
 - Area 4: Power / High-speed Devices and Materials
 - Area 5: Photonics: Devices / Integration / Related Technology
 - Area 6: Photovoltaics / Energy Harvesting / Battery-related Technology

- Area Scope
- Area 7: Organic / Molecular / Bio-electronics
 - Area 8: Low Dimensional Devices and Materials
 - Area 9: Novel Functional / Quantum / Spintronic Devices and Materials
 - Area 10: Thin Film Electronics: Oxide / Non-single Crystalline / Novel Process
 - Area 11: Advanced Materials: Synthesis / Crystal Growth / Characterization
 - Area 12: Advanced Circuits / Systems Interacting with Innovative Devices and Materials